TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK3475

VHF- and UHF-band Amplifier Applications

(Note)The TOSHIBA products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment. These TOSHIBA products are neither intended nor warranted for any other use. Do not use these TOSHIBA products listed in this document except for high frequency Power Amplifier of telecommunications equipment.

• Output power: Po = 630 mW (min)

• Gain: Gp = 14.9dB (min)

• Drain efficiency: $\eta_D = 45\%$ (min)

Maximum Ratings (Ta = 25℃)

1 2007-2-19